

A cross-sectional view of a semiconductor device. The device is built on a substrate 20. A gate stack 21 is formed on the substrate, comprising a gate 22, a gate sidewall 221, a gate bottom 222, a gate spacer 23, a gate contact 24, a gate electrode 25, a gate insulating layer 30, a gate conductive layer 31, and a gate metal layer 40. The gate metal layer 40 is connected to a gate metal contact 41.

FIG. 1

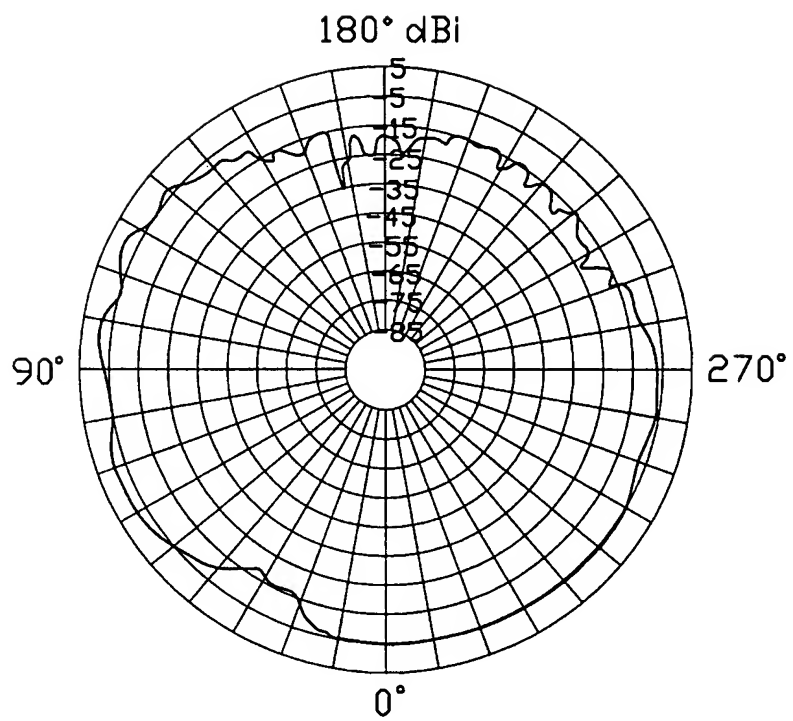


FIG. 2

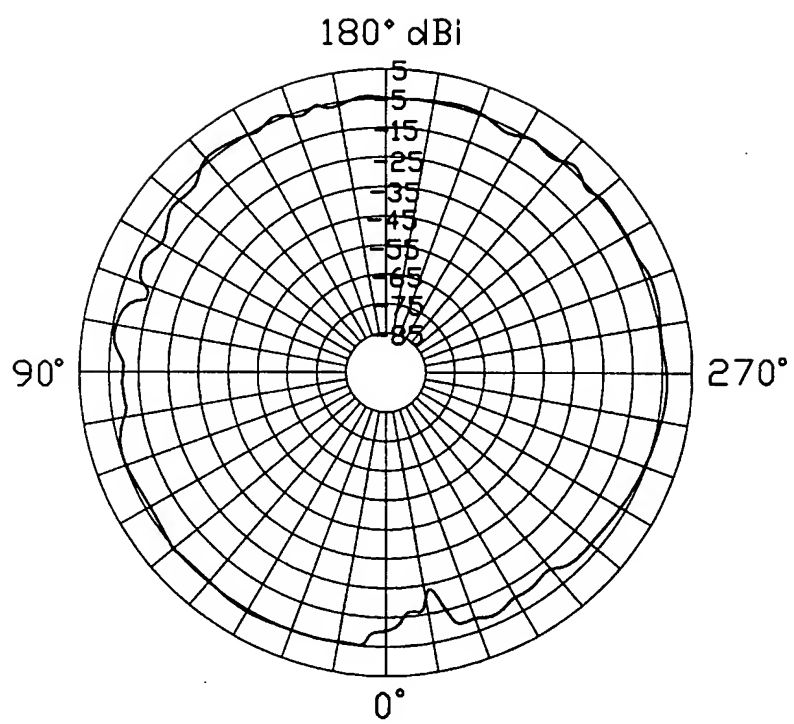


FIG. 3

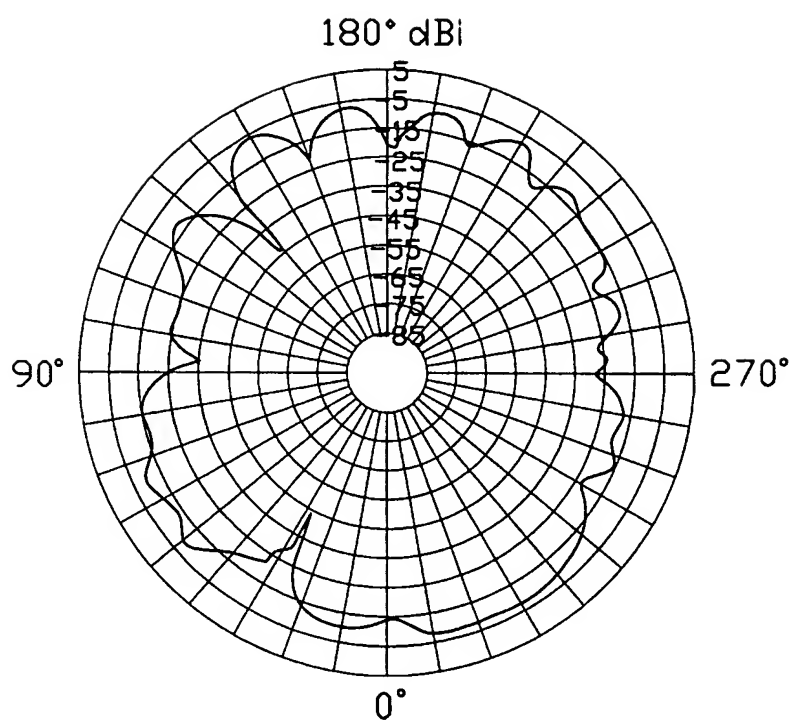


FIG. 4

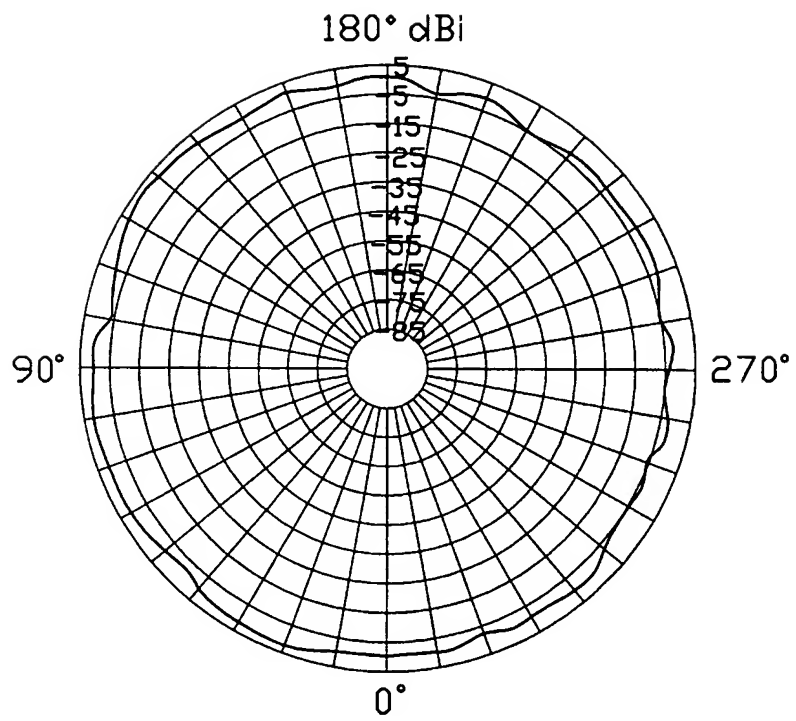


FIG. 5

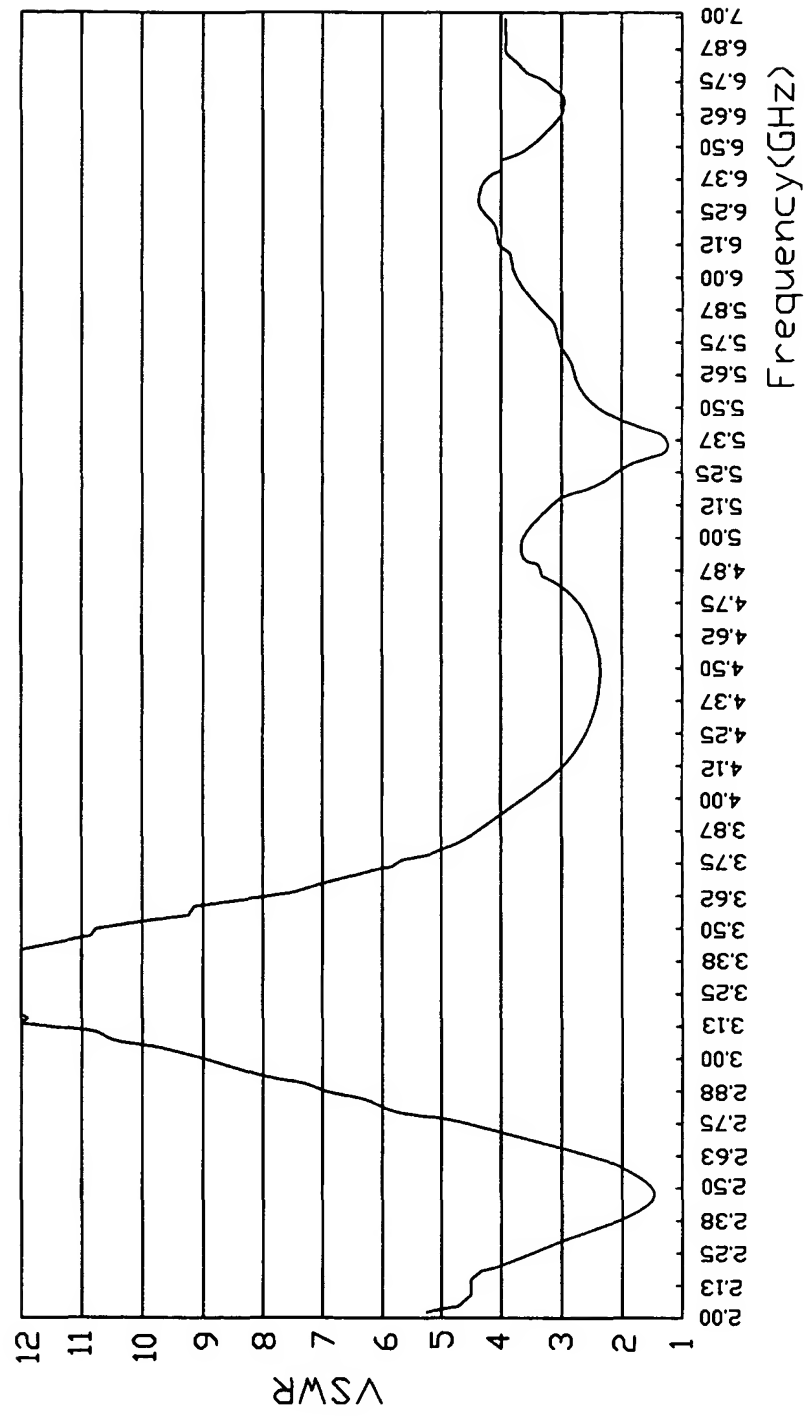


FIG. 6